

SDH60-14S

60A, 1400V Standard Rectifier

Features

- Typical Forward Voltage: $V_F=1.15V@ I_F=60A$
- Reverse Voltage: $V_{RRM}=1400V$
- Avalanche Energy Rated
- SIPOS+GPP double passivation

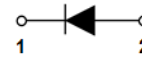
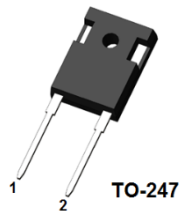
Description

The SDH60-14S is a Standard Rectifier. It's a SIPOS+GPP double passivation chip with high reliability. It has low leakage current and low forward voltage drop, Improved thermal behavior.

Applications

- Diode for main rectification
- For single and three phase
- Bridge configurations

Package Type & Internal Circuit



1. Anode 2.Cathode

Absolute Maximum Ratings per diode at $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter			Ratings	Unit
V _{RRM}	Peak Repetitive Reverse Voltage			1400	V
V _{RWM}	Working Peak Reverse Voltage			1400	V
V _R	DC Blocking Voltage			1400	V
I _{F(AV)}	Average Rectified Forward Current	per device at T _C =120℃		60	A
I _{FSM}	Non-repetitive Peak Surge Current	t = 10 ms (50 Hz), sine	T _{VJ} = 45℃ V _R = 0 V	720	A
			T _{VJ} = 150℃ V _R = 0 V	540	
I²t	value for fusing	t = 10 ms (50 Hz), sine	T _{VJ} = 45℃ V _R = 0 V	2590	A²S
			T _{VJ} = 150℃ V _R = 0 V	1460	
T _J	Operating Junction Temperature Range			-40~+150	℃
T _{STG}	Storage Temperature Range			-40~+150	℃

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$	Thermal Resistance, Junction to case	1.1	$^{\circ}C/W$

Electrical Characteristics per diode @ $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage Drop	$I_F=60A$	-	1.15	1.50	V
		$I_F=60A, T_C=120^{\circ}C$	-	-	1.2	V
I_R	Reverse Leakage Current	$V_R=1400V$	-	-	1	mA

Typical Performance Characteristics

Fig. 1. Typical Characteristics: V_F vs. I_F

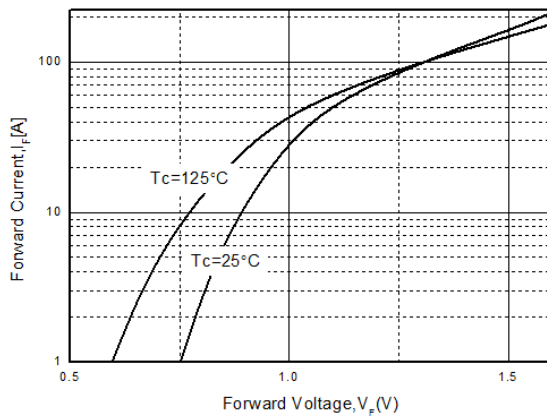


Fig. 2. Typical Characteristics: V_R vs. I_R

